

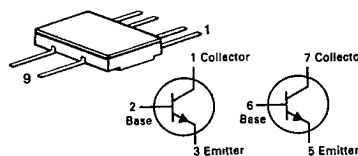
6367254 MOTOROLA SC (XSTRS/R F)

96D 82391 D

T-29-27

**2N3043  
thru  
2N3045  
2N3048**

CASE 610A-04, STYLE 1



**DUAL  
AMPLIFIER TRANSISTOR**  
NPN SILICON



**MAXIMUM RATINGS**

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	45		Vdc
Collector-Base Voltage	V <sub>CBO</sub>	45		Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0		Vdc
Collector Current — Continuous	I <sub>C</sub>	30		mAdc
		One Die	Both Die	
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	250 1.67	350 2.33	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	0.7 4.67	1.4 9.33	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)**

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage(1) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	45	—	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	—	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 45 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 45 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = +150°C)	I <sub>CBO</sub>	—	0.010 10	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	—	0.010	μAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain(1) (I <sub>C</sub> = 10 μAdc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	100	300	—
(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc)		50	200	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0.5 mAdc)	V <sub>CE(sat)</sub>	—	1.0	Vdc
Base-Emitter On Voltage (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc)	V <sub>BE</sub>	0.6	0.8	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Current-Gain — Bandwidth Product (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 20 MHz)	f <sub>T</sub>	30	—	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	—	8.0	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	3.2k 1.6k	19k 13k	Ohms
Small-Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	130 65	600 400	—
Output Admittance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 1.0 kHz)	h <sub>oe</sub>	—	100 70	μmhos
Noise Figure (I <sub>C</sub> = 10 μAdc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 10 kohms, Bandwidth = 10 Hz to 15.7 kHz)	NF	—	5.0	dB

MOTOROLA SMALL-SIGNAL SEMICONDUCTORS

6367254 MOTOROLA SC (XSTRS/R F)

96D 82392 D

2N3043 thru 2N3045, 2N3048

T-29-27

**ELECTRICAL CHARACTERISTICS** (continued) ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
<b>MATCHING CHARACTERISTICS</b>				
DC Current Gain Ratio(2) ( $I_C = 10 \mu\text{A dc}$ , $V_{CE} = 5.0 \text{ V dc}$ )	$h_{FE1}/h_{FE2}$	0.9 0.8	1.0 1.0	—
Base-Emitter Voltage Differential ( $I_C = 10 \mu\text{A dc}$ , $V_{CE} = 5.0 \text{ V dc}$ )	$ V_{BE1} - V_{BE2} $	— —	5.0 10	mVdc
Base-Emitter Voltage Differential Temperature Gradient ( $I_C = 10 \mu\text{A dc}$ , $V_{CE} = 5.0 \text{ V dc}$ , $T_A = -55$ to $+125^\circ\text{C}$ )	$\frac{\Delta(V_{BE1} - V_{BE2})}{\Delta T_A}$	— —	10 20	$\mu\text{V}^\circ\text{C}$

- (1) Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .  
 (2) The lowest  $h_{FE}$  reading is taken as  $h_{FE1}$  for this test.

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MOTOROLA SMALL-SIGNAL SEMICONDUCTORS

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